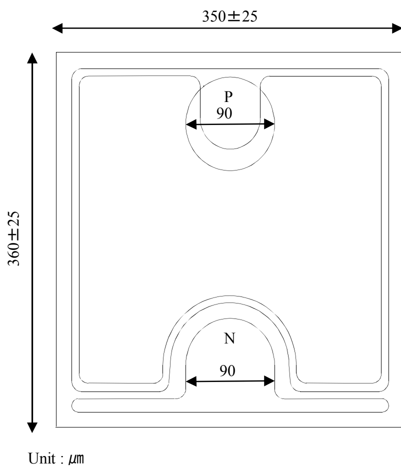
ULTRA VIOLET LED Chip C385-5SRA

(1) Chip Description

●**Mechanical Specification**

Description	Dimension
Bottom Area	350μm x360μm ± 25μm
Chip Thickness	120μm ± 10μm
N Bonding Pad Electrode	90μm ±5μm
P Bonding Pad Electrode	90μm ±5μm



Unit : μm

● **Material**

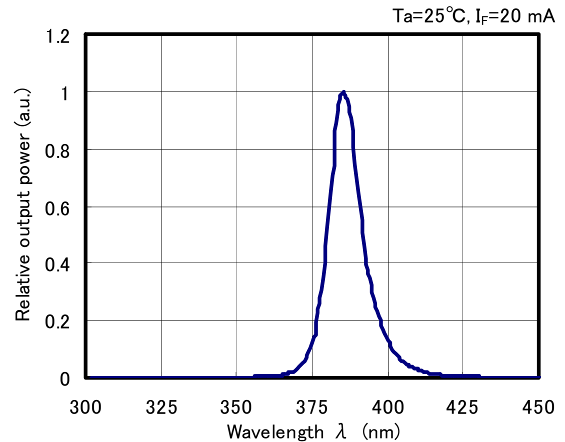
Substrate : Sapphire

Epitaxial Layer : GaN Based Material

N Bonding Pad Electrode : Au alloy

P Bonding Pad Electrode : Au alloy

(2) Spectrum



(3) Optical and Electrical Characteristics (Ta=25℃)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F=20mA	3.2	3.5	4.2	V
Reverse Current	I_R	V_R=5V	-	-	10	μA
Peak Wavelength*1	λ_p	I_F=20mA	380	-	390	nm
Full Width at Half Maximum	Δλ	I_F=20mA	10	-	20	nm
Optical Output Power *2	Po	I_F=20mA	7.0	-	8.0	mW

*1 Measurement error is ±2nm *2 Measurement error is ±10%

CAUTION

- LEDs emit very strong UV radiation.
- Don't look directly into the LED light. UV radiation can harm your eyes.
- To prevent even inadequate exposure, wear protective eyewear.
- If LEDs are embedded in devices, please indicate warning labels against the UV light LED used.
- Keep out of reach of children.
- UV LED chips are very sensitive to static and surge. Take a full protection from static.

Specification and dimension are subject to change for improvement without notice.

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